

Microsys International (S) Pte Limited

Parameters	Poly-crystalline silicon
Maximum power (watt) W	40W
Production tolerance	+3% /-3%
Maximum power voltage V	17.5V
Maximum power current A	2.28A
Open circuit voltage V	21V
Short circuit current A	2.33A
Size of module (wide and high)	610*510*28(MM)
Frame(type, material and thickness)	Anodized Alum. Alloy 28mm thickness
Number of cells	36pcs
Size of cells(wide and high)	156*156(MM)
Weight per piece KG	4
By pass Schottky diode(3pcs)	10A
Type of junction box	TUV certified junction box
Certificates	CE, ROHS
Cable type and length,	4cm ² TUV certified cable 1m long
connector type	Multi contact connector
	(compatible to MC type IV)
Maximum system voltage	1000V
Temperature coefficient of Isc	±0.05%℃
Temperature coefficient of Voc	-0.33%℃
Temperature coefficient of power	-0.5%℃
Temperature coefficient of Imp	+0.08%℃
Temperature coefficient of Vm	-0.33%℃
NOCT(nominal operating cell temperature)	45°C (±°C)
Insulation	> = 100MOhm
Voltage standoff	AC2000V, DC 3000V
Wind bearing	60m/s(200kg/sq.m)
Impact resistance hail impact test	227g steel ball fall down from 1m height
Encapsulated with toughened glass	Low iron tempered glass with thickness of
	3.2mm,light transmittance above91%
Superstrate in front	Hi-sheet RC 02B (0.45mm thick)/Japan
Backside foil	PTL3-38/75(0.17mm thick),Krempel/Germany
Conversion efficiency	Cell conversion efficiency > 15.75%
Quality guarantee	2years product warranty,10years 90% and 25years
	80% of the power